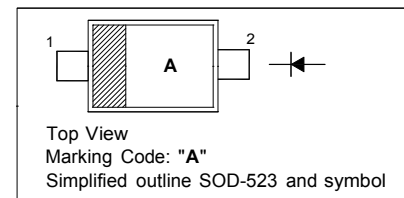


Silicon Epitaxial Planar Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

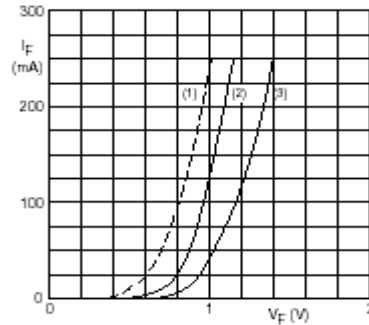


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	250	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1\text{ }\mu\text{s}$ 4	A
		at $t = 1\text{ ms}$ 1	
		at $t = 1\text{ s}$ 0.5	
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

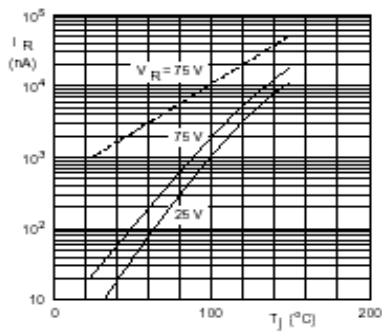
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit				
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 50\text{ mA}$ at $I_F = 150\text{ mA}$	V_F	715 855 1000 1250	mV				
Reverse Current at $V_R = 25\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 25\text{ V}, T_J = 150\text{ }^\circ\text{C}$ at $V_R = 75\text{ V}, T_J = 150\text{ }^\circ\text{C}$		I_R		30 1 30 50	nA μA μA μA		
Diode Capacitance at $V_R = 0\text{ V}, f = 1\text{ MHz}$				C_{tot}		1.5	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}, I_R = 1\text{ mA}, R_L = 100\text{ }\Omega$				t_{rr}		4	ns



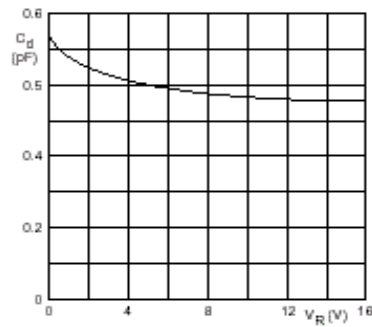
- (1) $T_j = 150\text{ }^\circ\text{C}$; typical values.
- (2) $T_j = 25\text{ }^\circ\text{C}$; typical values.
- (3) $T_j = 25\text{ }^\circ\text{C}$; maximum values.

Forward current as a function of forward voltage.



Dotted line: maximum values.
Solid lines: typical values.

Reverse current as a function of junction temperature.



$f = 1\text{ MHz}$; $T_j = 25\text{ }^\circ\text{C}$.

Diode capacitance as a function of reverse voltage; typical values.